

BUK6218-40C

N-channel TrenchMOS intermediate level FET Rev. 1 — 4 October 2010

Product data sheet

1. **Product profile**

1.1 General description

Intermediate level gate drive N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- AEC Q101 compliant
- Suitable for standard and logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoids
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	-	40	V
I _D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C};$ see <u>Figure 1</u>	-	-	42	Α
P _{tot}	total power dissipation	see Figure 2	-	-	60	W
Static characteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A};$ $T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 11}}{\text{ or } 100 \text{ m}}$	-	13.5	16	mΩ



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanche	valanche ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 42 A; $V_{sup} \le$ 40 V; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped	-	-	25	mJ
Dynamic ch	naracteristics					
Q_{GD}	gate-drain charge	I_D = 25 A; V_{DS} = 32 V; V_{GS} = 10 V; see <u>Figure 13</u> ; see <u>Figure 14</u>	-	7.7	-	nC

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	D
3	S	source		_G (民本)
mb	D	mounting base; connected to drain	1 3	mbb076 S
			SOT428 (DPAK)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK6218-40C	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	40	V
V_{GS}	gate-source voltage	Pulsed	<u>[1]</u>	-20	20	V
		DC	[2]	-16	16	V
I _D	drain current	$T_{mb} = 25 ^{\circ}C; V_{GS} = 10 V; \text{ see } \frac{\text{Figure 1}}{}$		-	42	Α
		T_{mb} = 100 °C; V_{GS} = 10 V; see <u>Figure 1</u>		-	30	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; $t_p \le 10 \mu s$; pulsed; see <u>Figure 3</u>		-	168	Α
P _{tot}	total power dissipation	see <u>Figure 2</u>		-	60	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drain	diode					
Is	source current	$T_{mb} = 25 ^{\circ}C$		-	42	Α
I _{SM}	peak source current	$t_p \le 10 \mu\text{s}; \text{ pulsed}; T_{mb} = 25 ^{\circ}\text{C}$		-	168	Α
Avalanche rug	ggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$I_D = 42 \text{ A}$; $V_{\text{sup}} \le 40 \text{ V}$; $V_{\text{GS}} = 10 \text{ V}$; $T_{j(\text{init})} = 25 ^{\circ}\text{C}$; unclamped		-	25	mJ
E _{DS(AL)R}	repetitive drain-source avalanche energy		[3][4][5]	-	-	J

^[1] Accumulated pulse duration not to exceed 5 minutes.

^{[2] -16}V accumulated duration not to exceed 168 hrs

^[3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

^[4] Repetitive avalanche rating limited by an average junction temperature of 170 °C.

^[5] Refer to application note AN10273 for further information.

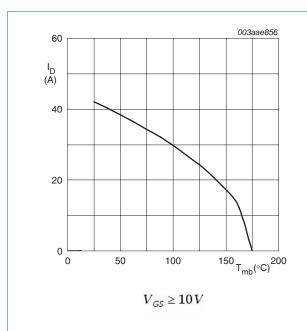


Fig 1. Continuous drain current as a function of mounting base temperature

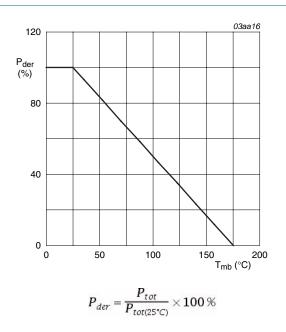
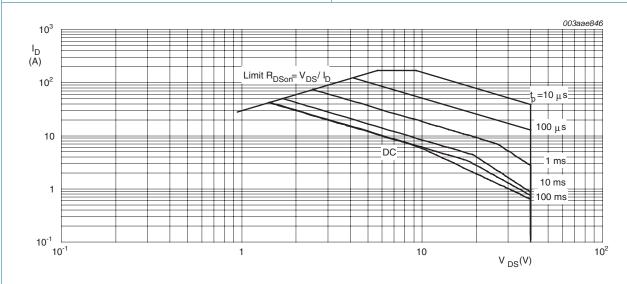


Fig 2. Normalized total power dissipation as a function of mounting base temperature



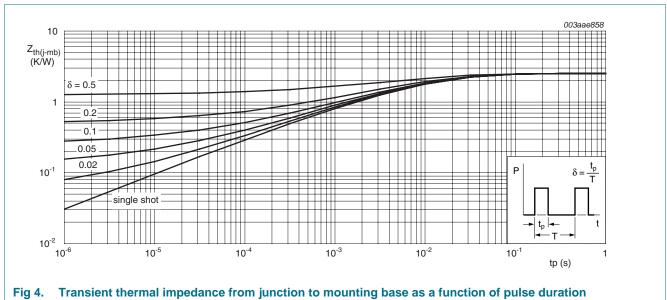
 $T_{mb} = 25$ °C; I_{DM} is a single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

Thermal characteristics

Table 5. **Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	2.52	K/W



6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	40	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	36	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 25 \text{ °C}$; see <u>Figure 9</u> ; see <u>Figure 10</u>	1.8	2.3	2.8	V
		$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = -55 \text{ °C}$; see <u>Figure 9</u>	-	-	3.3	V
		$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 175 \text{ °C}$; see <u>Figure 9</u>	0.8	-	-	V
I _{DSS}	drain leakage current	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μΑ
		$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
I_{GSS}	gate leakage current	$V_{DS} = 0 \text{ V}; V_{GS} = 20 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
		$V_{DS} = 0 \text{ V}; V_{GS} = -20 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 10 A; T_{mb} = 25 °C; see <u>Figure 11</u>	-	13.5	16	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 11</u>	-	20.7	28	mΩ
		V_{GS} = 5 V; I_D = 10 A; T_{mb} = 25 °C; see <u>Figure 11</u>	-	18.4	23	mΩ
		V_{GS} = 10 V; I_D = 10 A; T_j = 175 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	-	34	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}$; $V_{DS} = 32 \text{ V}$; $V_{GS} = 10 \text{ V}$; see <u>Figure 13</u> ; see <u>Figure 14</u>	-	22	-	nC
		$I_D = 25 \text{ A}$; $V_{DS} = 32 \text{ V}$; $V_{GS} = 5 \text{ V}$; see <u>Figure 13</u> ; see <u>Figure 14</u>	-	12.9	-	nC
Q_{GS}	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V};$	-	3.5	-	nC
Q_{GD}	gate-drain charge	see Figure 13; see Figure 14	-	7.7	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	873	1170	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 15</u>	-	134	161	pF
C _{rss}	reverse transfer capacitance		-	101	140	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V};$	-	7.4	-	ns
t _r	rise time	$R_{G(ext)} = 10 \Omega$	-	20.8	-	ns
t _{d(off)}	turn-off delay time		-	30.6	-	ns
t _f	fall time		-	20.1	-	ns
L _D	internal drain inductance	measured from upper edge of drain mounting base to centre of die; $T_j = 25 ^{\circ}\text{C}$	-	3.5	-	nΗ
L _S	internal source inductance	T _j = 25 °C; measured from source lead to source bond pad.	-	7.5	-	nΗ

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-drain diode						
V _{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 16</u>	-	0.9	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$ $V_{DS} = 25 \text{ V}$	-	34	-	ns
Q _r	recovered charge		-	35.9	-	nC

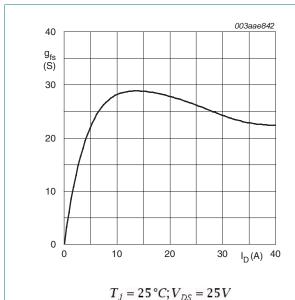


Fig 5. Forward transconductance as a function of drain current; typical values

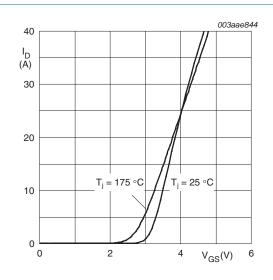
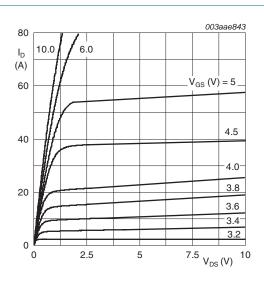


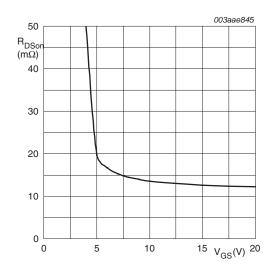
Fig 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values

 $V_{DS} > I_D \times R_{DSon}$



 $T_j = 25 \,^{\circ}C$

Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



 $T_j=25\,^{\circ}C; I_D=10A$

Fig 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

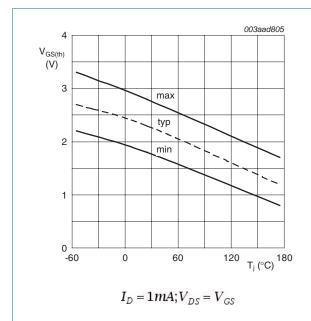


Fig 9. Gate-source threshold voltage as a function of junction temperature

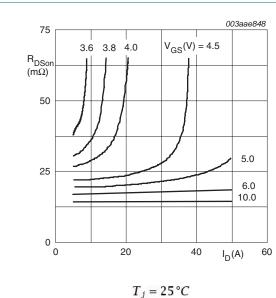


Fig 11. Drain-source on-state resistance as a function of drain current; typical values

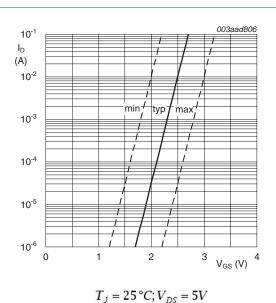


Fig 10. Sub-threshold drain current as a function of gate-source voltage

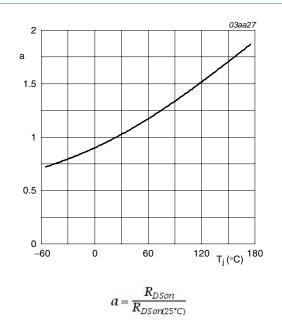


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

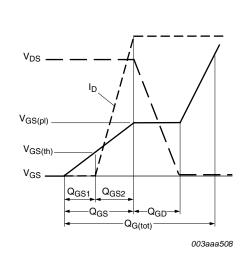
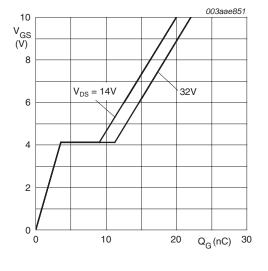


Fig 13. Gate charge waveform definitions



 $T_j = 25 \,^{\circ}C; I_D = 25A$

Fig 14. Gate-source voltage as a function of gate charge; typical values

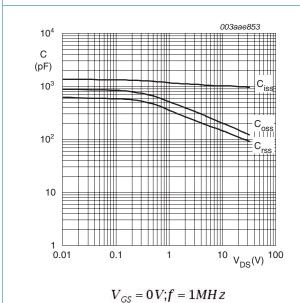


Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

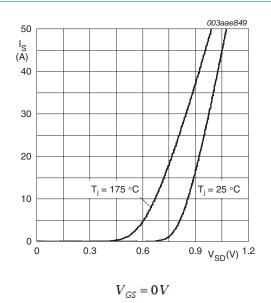


Fig 16. Source current as a function of source-drain voltage; typical values

7. Package outline

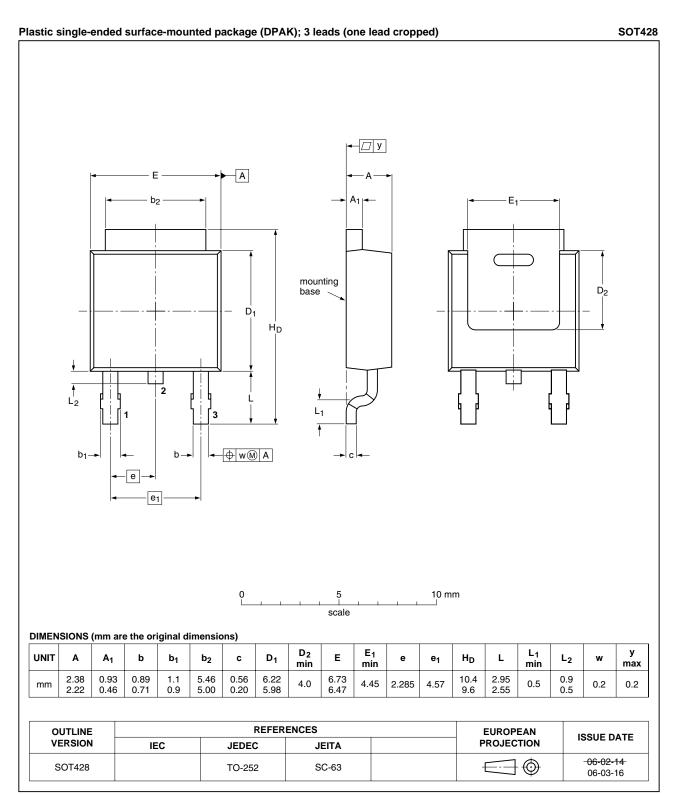


Fig 17. Package outline SOT428 (DPAK)

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N-channel TrenchMOS intermediate level FET

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK6218-40C v.1	20101004	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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11. Contents

1	Product profile	1
1.1	General description	1
1.2	Features and benefits	1
1.3	Applications	1
1.4	Quick reference data	1
2	Pinning information	2
3	Ordering information	2
4	Limiting values	3
5	Thermal characteristics	5
6	Characteristics	6
7	Package outline	0
8	Revision history1	1
9	Legal information1	2
9.1	Data sheet status	2
9.2	Definitions1	2
9.3	Disclaimers	2
9.4	Trademarks1	
10	Contact information	2

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